

1. Scope :

This specification applies to P/N silicon TVS diode chips,
Device NO. SD-11608

2. Structure :

- 2-1. Planar type : P/N Diode.
- 2-2. Electrodes :
Top side : Aluminum alloy.
Back side : Gold layer.

3. Size :

- 3-1. Chip size : 26.3 mils x 9.8 mils (0.670 mm x 0.250 mm).
- 3-2. Chip thickness : 5.9 ± 1.0 mils (0.150 ± 0.0254 mm)
- 3-3. Bonding pad : 21.7 mils x 5.1 mils (0.550 mm x 0.130 mm).
- 3-4. Pattern drawing : Refer to the attached drawing.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Reverse Working Voltage	V _{RWM}			5	V	-
Reverse Current	I _R			2000	nA	V _R =5V E _e =0mW/cm ²
Reverse Breakdown Voltage	V _(BR)	7		9	V	I _R =5mA E _e =0mW/cm ²
Capacitance	C _T		209		pF	F=1MHZ, V _R =0V
Reverse Clamping Voltage <i>*IEC6100-4-5 Standard.</i>	V _C		7.5		V	I _{PP} =1A T _p =8/20us
			8.2		V	I _{PP} =4A T _p =8/20us
Forward Voltage	V _f			1.2	V	I _F =10mA E _e =0mW/cm ²

Parameter	Symbol	Rating	Unit
ESD Voltage Air <i>*IEC6100-4-2 Standard.</i>	V _{ESD}	30	KV
ESD Voltage Contact <i>*IEC6100-4-2 Standard.</i>		30	

**AEC-Q101 qualified.*

